

INS8048-Series Microcomputer/Microprocessor Family

General Description

The INS8048/49/50-Series microcomputers and the INS8035/39/40-Series microprocessors (hereinafter referred to as the 48-Series) are self contained, 8-bit parallel, 40-pin, dual in-line devices fabricated using National Semiconductor's scaled N-channel, silicon gate MOS process, XMOS. The 48-Series devices contain the system timing, control logic, ROM (where applicable) program memory, RAM data memory and 27 I/O lines necessary to implement dedicated control functions. All 48-Series devices are pin compatible, differing only in the size of on-board ROM (where applicable) and RAM as shown below:

DEVICE	RAM ARRAY	ROM ARRAY
INS8048	64 x 8	1K x 8
INS8049	128 x 8	2K x 8
INS8050	256 x 8	4K x 8
INS8035	64 x 8	N/A
INS8039	128 x 8	N/A
INS8040	256 x 8	N/A

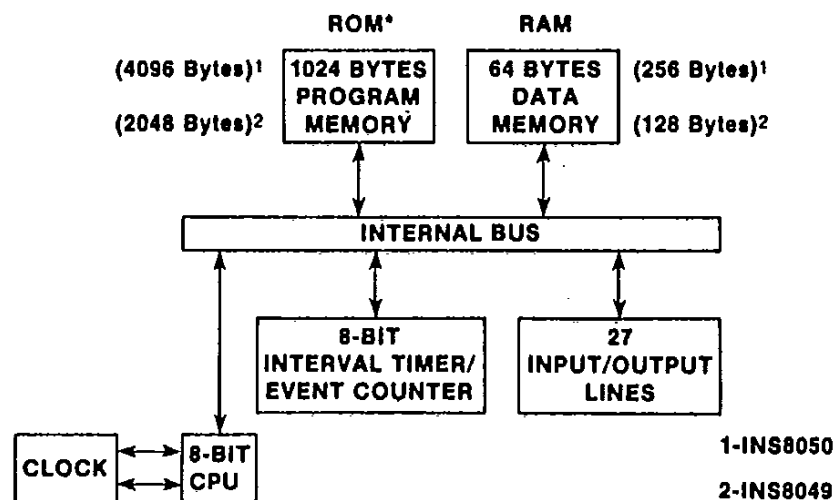
The devices are designed to be efficient controllers. They have extensive bit handling capability as well as facilities for both binary and BCD arithmetic. Efficient use of program memory is derived from an instruction set comprised predominantly of single bytes. The remaining instructions are two bytes in length. Additional external memory may be added up to a maximum of 4K bytes of program memory and 256 bytes of data memory without paging.

Features

- 8-Bit CPU, RAM, ROM, I/O in Single Package
- 2.5 μ sec Cycle, 6 MHz Clock; 1.36 μ sec Cycle, 11 MHz Clock
- On-Chip Oscillator Circuit and Clock (or External Source)
- 27 I/O Lines
- Expandable Memory and I/O
- 8-Bit Timer/Counter
- Single Level Interrupt
- Interrupt has Schmitt Trigger with Hysteresis*
- Over 90 Instructions (Most Single Byte)
- Binary and BCD Arithmetic
- Single 15V Power Supply
- Low Standby Power Mode*
- Low Voltage Standby (2.2V Min)*
- On-Chip Battery Charging*

*NOTE: Transparent improvements over industry standard part.

48-Series Block Diagram



*Not Applicable to INS8035/39/40

Absolute Maximum Ratings

Temperature Under Bias 0°C to +70°C
 Storage Temperature..... -65°C to +150°C
 All Input or Output Voltages with respect V_{SS} -0.5V to +7.0V
 Power Dissipation..... 1.5 Watt

NOTE: Absolute maximum ratings indicate limits beyond which permanent damage may occur. Continuous operation at these limits is not intended; operation should be limited to those conditions specified under DC Electrical Characteristics.

DC Electrical Characteristics

T_A = 0° C to +70° C, V_{CC} = +5V ±10%, V_{SS} = 0V, unless otherwise specified.

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
V _{IL}	Input Low Voltage (All except XTAL1, XTAL2)	-0.5		0.8	V	
V _{IL1}	Input Low Voltage (XTAL1, XTAL2)	-0.5		0.6	V	
V _{IH}	Input High Voltage	2.0		V _{CC}	V	
V _{IH1}	Input High Voltage (RESET, XTAL1, XTAL2)	3.0		V _{CC}	V	
V _{OL}	Output Low Voltage			0.4	V	I _{OL} = 2.0mA
V _{OH}	Output High Voltage All except ports 1 and 2	3.0		V _{CC}	V	I _{OH} = 100 μA
V _{OH1}	Port TTL	2.4			V	I _{OH} ≥ 125 μA
I _{IL}	Input Leakage Current (T1, EA, INT)			±10	μA	V _{SS} ≤ V _{IN} ≤ V _{CC}
I _{OL}	Output Leakage Current (BUS, T0) (High Impedance State)			-10.0	μA	V _{CC} ≥ V _{IN} ≥ V _{SS} + 0.45
I _{DD} (64)	64 words on Standby Current (2)			2.5	mA	8048
I _{DD} (128)	128 words on Standby Current (2)			4.5	mA	8049
I _{DD} (256)	256 words on Standby Current (2)			8.5	mA	8050
I _{DD} +I _{CC}	Total Supply Current 8048		30	65	mA	T _A = 25°C
I _{DD} +I _{CC}	Total Supply Current 8048L		25	40	mA	T _A = 25°C
I _{DD} +I _{CC}	Total Supply Current 8049		32	70	mA	T _A = 25°C
I _{DD} +I _{CC}	Total Supply Current 8049L		30	45	mA	T _A = 25°C
I _{DD} +I _{CC}	Total Supply Current 8050		35	75	mA	T _A = 25°C
I _{DD} +I _{CC}	Total Supply Current 8050L		35	50	mA	T _A = 25°C
I _{DDC}	Battery Charging Current			TBD	mA	See Figure 5
V _{DD}	Standby Power Supply	2.4		V _{CC}	V	See Figure 5

- Notes:**
- The Series-48 family of parts are also available in Industrial Temperature Range -40°C to +80°C. Industrial Temperature Range versions are denoted with an I following the part number (i.e., INS8048-6XXX/NI).
 - The low power versions (L parts), and the Industrial Temperature Range (I parts), are currently available throughout the Series-48 Family.

AC Electrical Characteristics - INS80XX-6 (1-6 MHz part)

$T_A = 0^\circ \text{C}$ to $+70^\circ \text{C}$, $V_{CC} = +5\text{V} \pm 10\%$, $V_{SS} = 0\text{V}$, unless otherwise specified.

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
tLL	ALE Pulse Width	400			ns	Note 1
tAL	Address Setup to ALE	150			ns	Note 1
tLA	Address Hold from ALE	80			ns	Note 1
tCC	Control Pulse Width $\overline{\text{PSEN}}$, $\overline{\text{RD}}$, $\overline{\text{WR}}$	700			ns	Note 1
tDW	Data Set-Up Before $\overline{\text{WR}}$	500			ns	Note 1
tWD	Data Hold After $\overline{\text{WR}}$	120			ns	$C_L = 20 \text{ pF}$
tCY	Cycle Time	2.5		15.0	μs	1 to 6 MHz XTAL
tDR	Data Hold	0		200	ns	Note 1
tRD	$\overline{\text{PSEN}}$, $\overline{\text{RD}}$ to Data In			500	ns	Note 1
tAW	Address Setup to $\overline{\text{WR}}$	230			ns	Note 1
tAD	Address Setup to Data In			950	ns	Note 1
tAFC	Address Float to $\overline{\text{RD}}$, $\overline{\text{PSEN}}$	0			ns	Note 1
tCA	Control Pulse to ALE	10			ns	Note 1

Port 2 Timing

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
tCP	Port Control Setup before Falling Edge of PROG	110			ns	Note 1
tPC	Port Control Hold after Falling Edge of PROG	140			ns	Note 1
tPR	PROG to Time P2 Input must be Valid			810	ns	Note 1
tDP	Output Data Setup Time	250			ns	Note 1
tPD	Output Data Hold Time	65			ns	Note 1
tPF	Input Data Hold Time	0		150	ns	Note 1
tPP	PROG Pulse Width	1510			ns	Note 1
tPL	Port 2 I/O Data Setup	400			ns	Note 1
tLP	Port 2 I/O Data Hold	150			ns	Note 1

AC Electrical Characteristics - INS80XX-11 (4-11 MHz Part)

$T_A = 0^\circ \text{C}$ to $+70^\circ \text{C}$, $+5\text{V} \pm 10\%$, $V_{SS} = 0\text{V}$, unless otherwise specified.

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
tLL	ALE Pulse Width	150			ns	Note 1
tAL	Address Setup to ALE	70			ns	Note 1
tLA	Address Hold from ALE	50			ns	Note 1
tCC	Control Pulse Width $\overline{\text{PSEN}}$, $\overline{\text{RD}}$, $\overline{\text{WR}}$	300			ns	Note 1
tDW	Data Set-Up Before $\overline{\text{WR}}$	250			ns	Note 1
tWD	Data Hold After $\overline{\text{WR}}$	40			ns	$C_L = 20 \text{ pF}$
tCY	Cycle Time	1.36		3.75	μs	4 to 11 MHz XTAL
tDR	Data Hold	0		100	ns	Note 1
tRD	$\overline{\text{PSEN}}$, $\overline{\text{RD}}$ to Data In			200	ns	Note 1

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AC Electrical Characteristics - INS80XX-11 (Cont'd.)

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
t _{AW}	Address Set-Up to \overline{WR}	200			ns	Note 1
t _{AD}	Address Set-up to Data In			400	ns	Note 1
t _{AFC}	Address Float to \overline{RD} , \overline{PSEN}	-10			ns	Note 1
t _{CA}	Control Pulse to ALE	10			ns	Note 1

Port 2 Timing

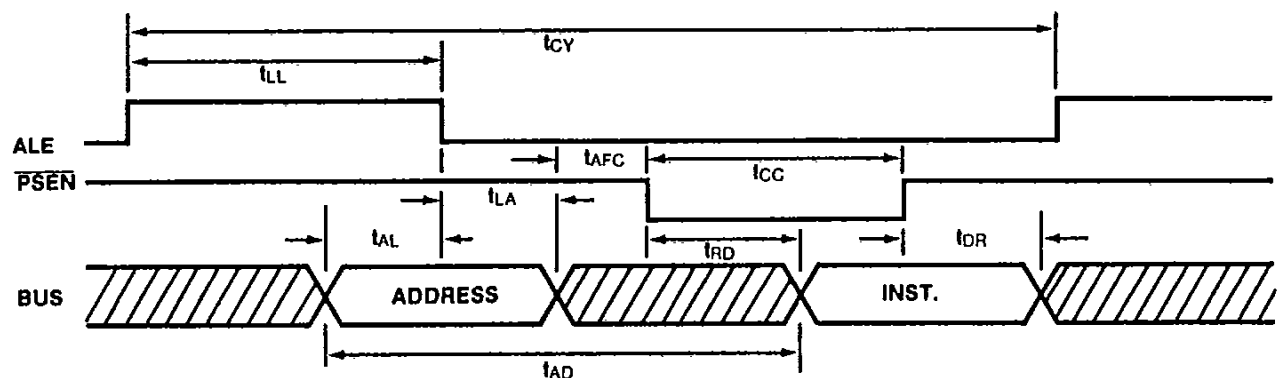
Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
t _{CP}	Port Control Setup before Falling Edge of PROG	100			ns	Note 1
t _{PC}	Port Control Hold after Falling Edge of PROG	60			ns	Note 1
t _{PR}	PROG to Time P2 Input must be Valid			650	ns	Note 1
t _{DP}	Output Data Setup Time	200			ns	Note 1
t _{PD}	Output Data Hold Time	20			ns	Note 1
t _{PF}	Input Data Hold Time	0		150	ns	Note 1
t _{PP}	PROG Pulse Width	700			ns	Note 1
t _{PL}	Port 2 I/O Data Setup	150			ns	Note 1
t _{LP}	Port 2 I/O Data Hold	20			ns	Note 1

Note 1. Control outputs $C_L = 80$ pF; Bus outputs $C_L = 150$ pF

Capacitance $T_A = 25^\circ \text{C}$, $V_{CC} = V_{SS} = 0\text{V}$

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
C _{IN}	Input Capacitance		6	10	pF	$f_c = 1$ MHz
C _{OUT}	OUTPUT AND \overline{RESET} Capacitance		10	20	pF	Unmeasured pins returned to V _{SS}

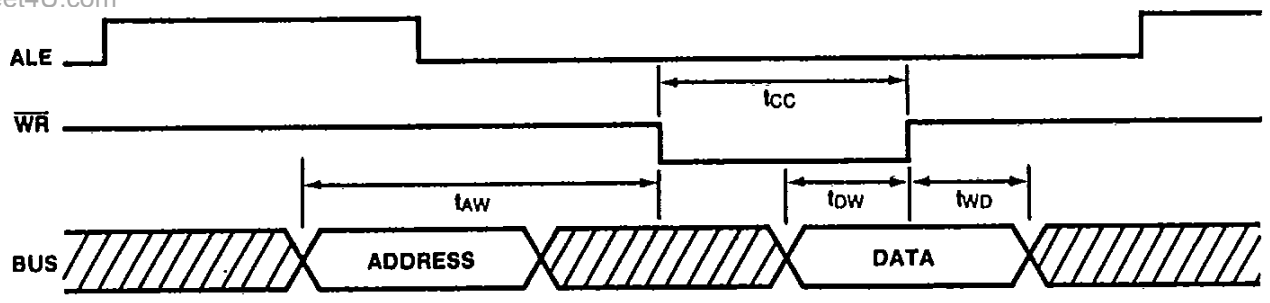
Timing Waveforms



Instruction Fetch from External Program Memory

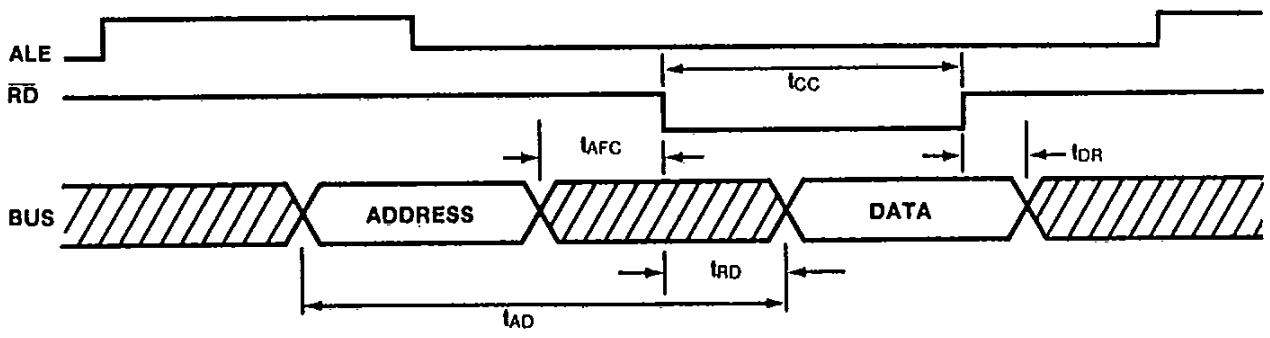
12-14

NOTE: Diagonal lines indicate interval of high impedance.



Write to External Data Memory

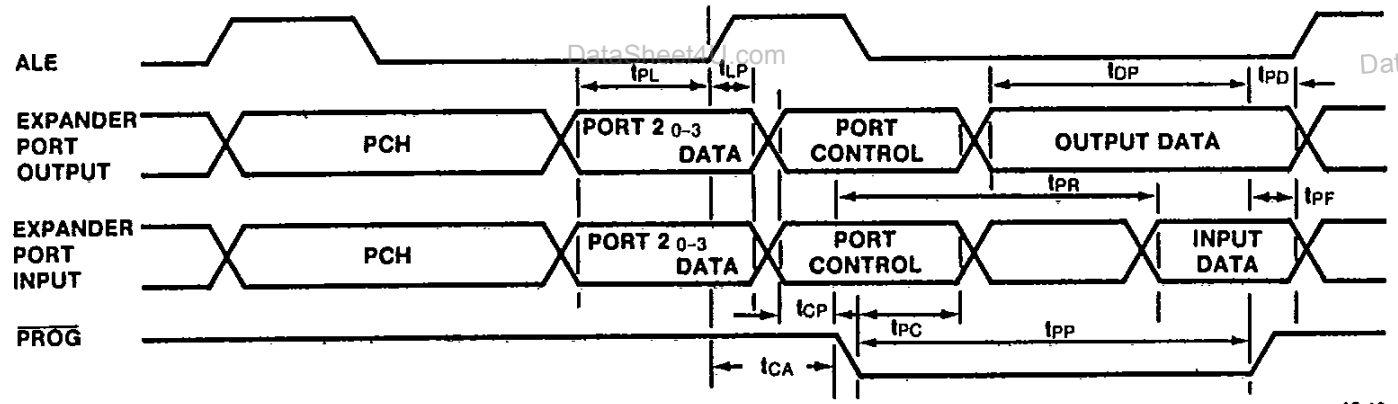
12-15



Read from External Data Memory

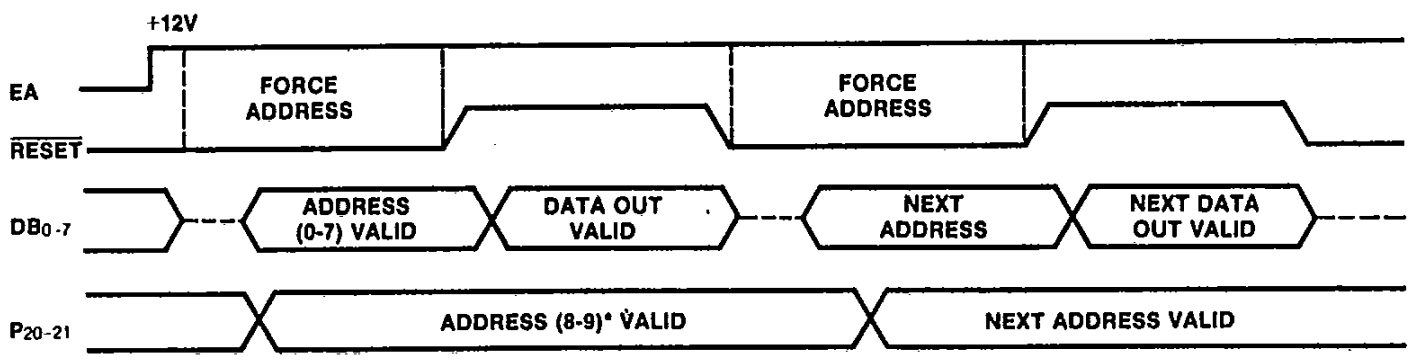
NOTE: Diagonal lines indicate interval of high impedance.

12-11



Port 2 Timing

12-12



Verify Mode Timing

8049 = 8-10
8050 = 8-11

Functional Pin Description

INPUT SIGNALS

Reset ($\overline{\text{RESET}}$): An active low (0) input that initializes the processor and is used to verify program memory. (See note #1.)

Single Step ($\overline{\text{SS}}$): Active low (0) input which, in conjunction with ALE, can single step the processor through each instruction.

External Access (EA): An active high (1) input that forces all program memory fetches to reference external program memory.

Testable Input 0 (T_0): Testable input pin using conditional branch functions JT0 ($T_0 = 1$) or JNT0 ($T_0 = 0$). T_0 can be designated as the clock output using instruction ENT0 CLK.

Testable Input 1 (T_1): Testable input pin using conditional branch functions JT1 ($T_1 = 1$) or JNT1 ($T_1 = 0$). T_1 can be designated as the Timer/Counter input from an external source using instruction STRT CNT.

Interrupt ($\overline{\text{INT}}$): An active low input that initiates an interrupt when interrupt is enabled. Interrupt is disabled after a reset. Also can be tested with instruction JINI ($\overline{\text{INT}} = 0$). (See Note 2).

OUTPUT SIGNALS

Read Strobe ($\overline{\text{RD}}$): An active low output strobe activated during a Bus read. Can be used to enable data onto the BUS from an external device. Used as a Read Strobe to External Data Memory.

Write Strobe ($\overline{\text{WR}}$): An active low output strobe activated during a Bus write. Used as a Write Strobe to External Data Memory.

Program Store Enable ($\overline{\text{PSEN}}$): An active low output that occurs only during an external program memory fetch.

Address Latch Enable (ALE): An active high output that occurs once during each cycle and is useful as a clock output. The negative going edge of ALE strobes the address into external data or program memory.

Program (PROG): This output (active high) provides the output strobe for INS8243 I/O Expander.

INPUT/OUTPUT SIGNALS

Crystal Input (XTAL1, XTAL2): These two pins connect the crystal for internal oscillator operation. XTAL1 is the timing input for external source.

Port 1 (P10-P17): 8-bit quasi-bidirectional port.

Port 2 (P20-P27): 8-bit quasi-bidirectional port. During an external program memory fetch, the four high-order program counter bits occur at P20-P23. They also serve as a 4-bit I/O expander bus when the INS8243 I/O Expander is used. (See note 3).

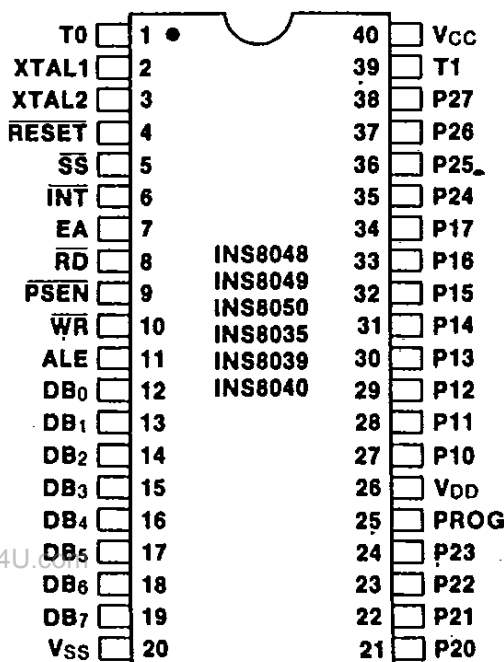
BUS (DB₀-DB₇): True bidirectional port, either statically latched or synchronous. Can be written to using $\overline{\text{WR}}$ Strobe, or Read from using $\overline{\text{RD}}$ Strobe. During an external program memory fetch, the 8 lower order program counter bits are preset at this port. The addressed instruction appears on this bus when $\overline{\text{PSEN}}$ is low. During an external RAM data store instruction. This port presents address and data under control of ALE, $\overline{\text{RD}}$, and $\overline{\text{WR}}$.

V_{SS}: Processor Ground potential.

V_{DD}: V_{DD} functions as the Low Power Stand-by Voltage and can vary from 2.2V to 5.5V.

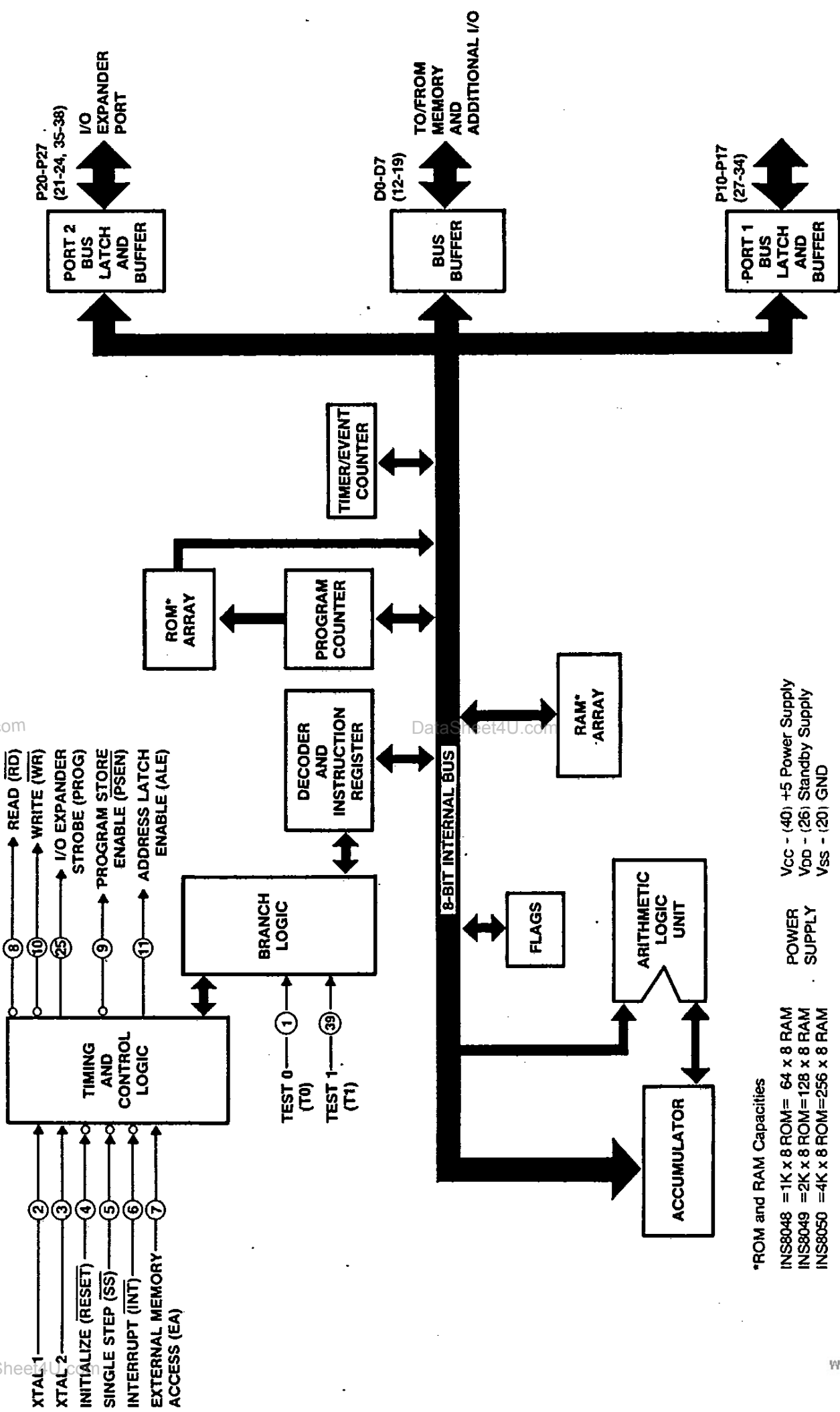
V_{CC}; Pin 40: Primary Power Source for 48-Series Devices.

Pin Configuration



Functional Description

The following paragraphs contain the functional description of the major elements of the 48-Series microcomputer/microprocessor. Figure 1 is a block diagram of the 48-Series devices. The data paths are illustrated in simplified form to show how the various logic elements communicate with each other to implement the instruction set common to all devices.



*ROM and RAM Capacities
 INS8048 = 1K x 8 ROM = 64 x 8 RAM
 INS8049 = 2K x 8 ROM = 128 x 8 RAM
 INS8050 = 4K x 8 ROM = 256 x 8 RAM

POWER SUPPLY VCC - (40) +5 Power Supply
 VDD - (26) Standby Supply
 VSS - (20) GND

Note: Applicable pinout numbers are included within parentheses.

FIGURE 1. 48-Series Block Diagram

Program Memory

The Program Memory (ROM) contained on the INS8048/49/50 devices is comprised of 1024, 2048 or 4096 8-bit bytes, respectively. As is seen by examining the 48-Series instruction set, these bytes may be program instructions, program data or ROM addressing data. The ROM for the above devices must be mask programmed at the National Semiconductor factory. The ROMless microprocessors, INS8035, INS8039 and INS8040 use external program memory. This makes program development straightforward using standard UV erasable PROMs to emulate a possible future single chip (using the on-board ROM) system. ROM addressing, up to a maximum of 4K, is accomplished by a 12-bit Program Counter (PC). The INS8048 and INS8049 will automatically address external memory when the boundary of their internal memories, 1K and 2K respectively, are exceeded. The binary value of the address selects one of the 8-bit bytes contained in ROM. A new address is loaded into the PC register during each

instruction cycle. Unless the instruction is a transfer of control instruction, the PC register is loaded with the next sequential binary count value.

With reference to the Program Memory Map (see *Figure 2*) there are three ROM addresses which provide for the control of the microcomputer.

1. Memory Location 0000 - Resetting the Reset (negative true) input to the microcomputer forces the first instruction to be fetched from address 0000.
2. Memory Location 0003 - Asserting the Interrupt (negative true) input to the microcomputer (when interrupt is enabled) forces a jump to subroutine.
3. Memory Location 0007 - A timer/counter interrupt that results from timer/counter overflow (when enabled) forcing a jump to subroutine.

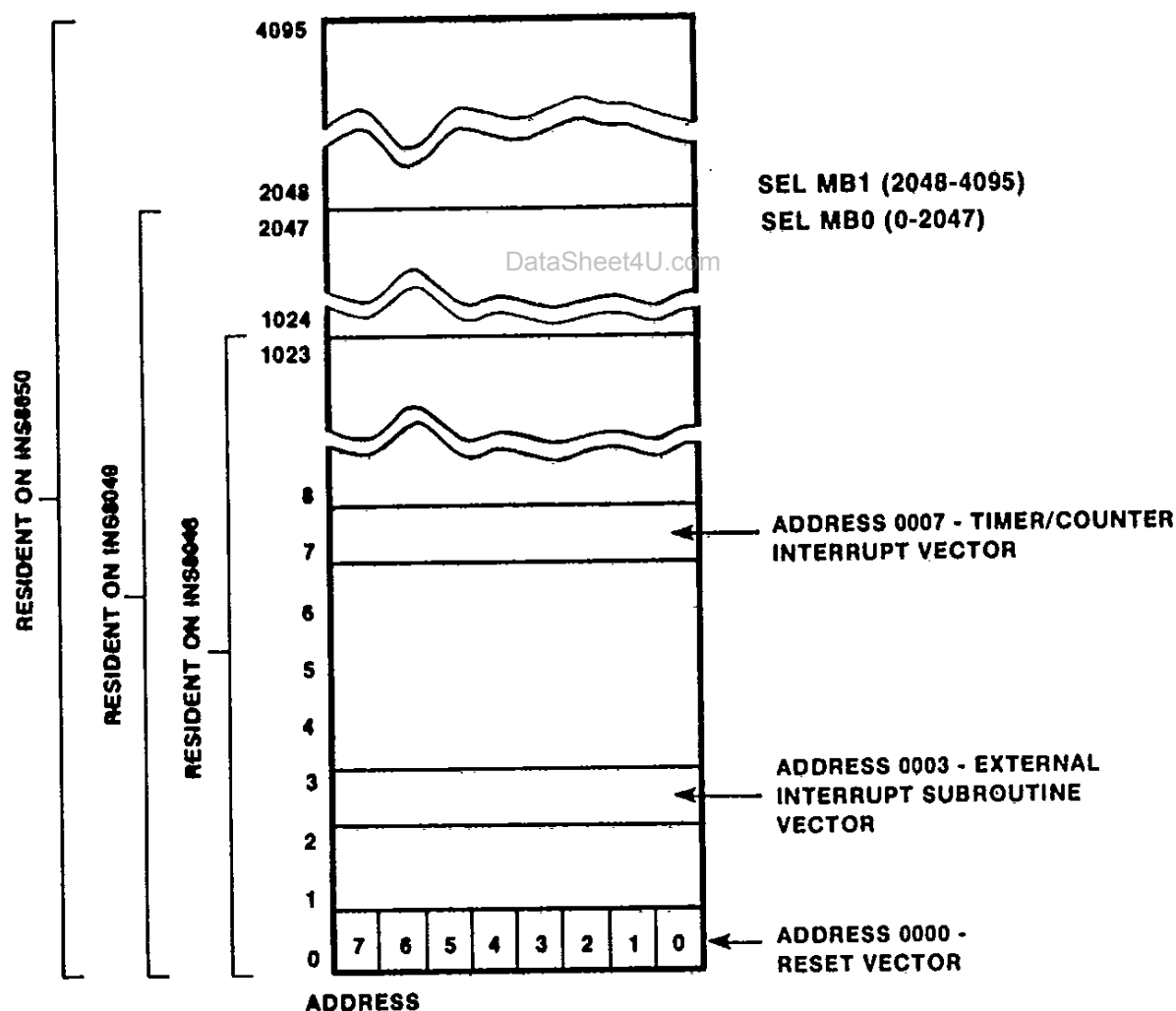


FIGURE 2. INS8048/49/50 Resident ROM Program Memory Map

Data Memory (RAM)

The resident RAM data memory is arranged as 64 (INS8035/8048), 128 (INS8039/8049) or 256 (INS8040/8050) bytes. RAM addressing is implemented indirectly via either of two 8-bit RAM pointer registers R0 and R1. These pointer registers are essentially the first two locations in the RAM (see *Figure 3*), addresses 000 and 001. RAM addressing may also be performed directly by 11 direct register instructions. The pointer register area of the RAM array is made up of eight working registers that occupy either the first bank (0), locations (0 to 7), or the second bank (1), locations 24-31. The second bank of working registers is selected by using the Register Bank Switch instruction (SEL RB). If this bank is not used for working registers, it can be used as user RAM.

There is an 8-level stack after Bank 0 that occupies address locations 8 to 23. These RAM locations are addressed indirectly through R0, R1 or the 3-bit Stack Pointer (SP). The stack pointer keeps track of the return address and pushes each return address down into the stack. There are 8 levels of subroutine nesting possible in the stack because each address occupies 10 bits or more using two bytes in RAM. When the level of subroutine nesting is less than 8, the stacks not used may be utilized as user RAM locations.

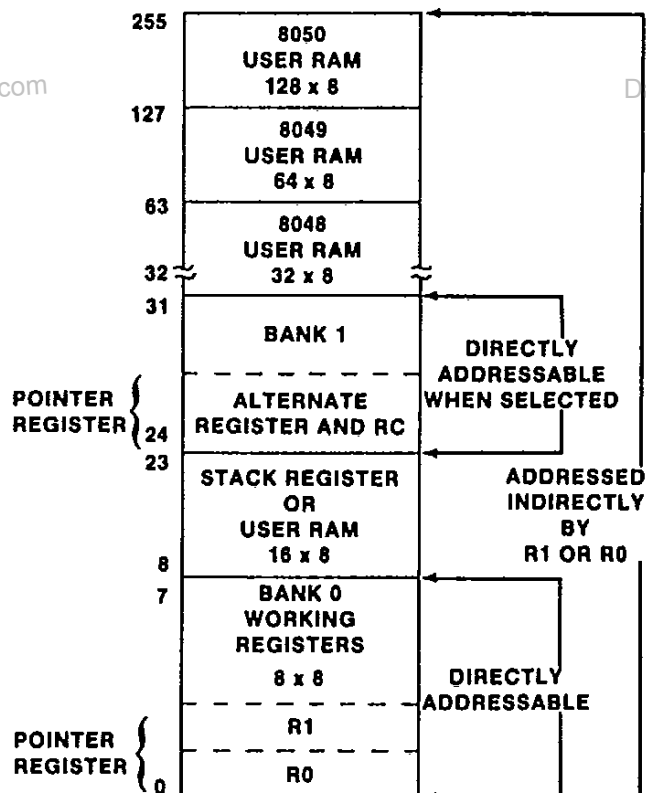


FIGURE 3. 48-Series Resident RAM Data Memory Map

Input/Output

The 48-Series devices have 27 lines of input/output organized as three, 8-bit ports plus three test inputs. The three ports may be used as inputs, outputs or bidirectional ports. Ports 1 and 2 differ from port 3 (Bus Port) in that they are quasi-bidirectional ports. Ports 1 and 2 can be used as input and output while being statically latched. If more I/O lines are required, Port 2 can also serve as a 4-bit I/O bus expander when used in conjunction with the INS8243 I/O Expander.

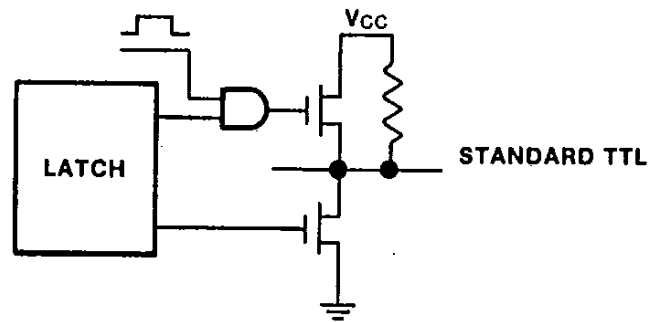


FIGURE 4. Input/Output Options

The bus port is a true bidirectional port and is either statically latched or synchronous. It can be written to using \overline{WR} strobe or read from using \overline{RD} strobe. During an external program memory fetch, the 8 lower order program counter bits are preset at this port. The addressed instruction appears on this bus when \overline{PSEN} is low. During an external RAM data store instruction, this port presents address and data under control of ALE, \overline{RD} , and \overline{WR} .

Transparent Improvements

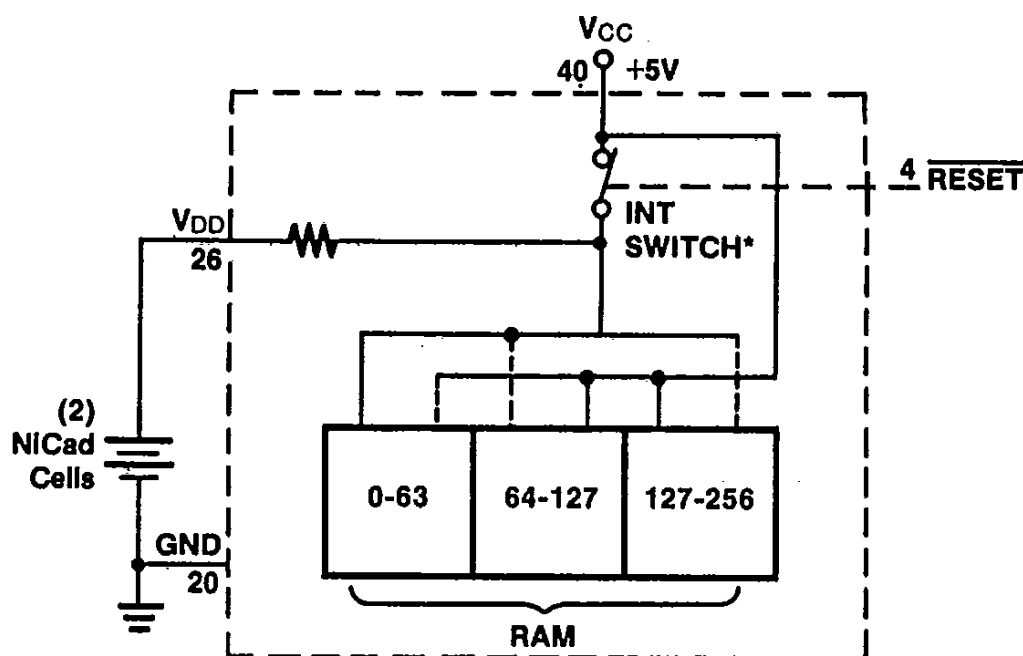
National has made some additional improvements to the standard industry parts. These include a battery charging circuit, and interrupt pin with hysteresis. Also, these improvements are transparent to the user. See Figure 5.

Power Down Mode

During the power down mode, V_{DD} which normally maintains the RAM cells, is the only pin that receives power. V_{CC} , which serves the CPU and ports is dropped from nominal 5 volts to 0 volt, after the CPU is reset, so that the RAM cells are unaltered by the loss of power. When power is restored, the processor goes through the normal power-on procedure.

Battery Charging Circuit

All 48-Series devices contain a circuit to provide external battery charging capabilities. Power for all on-board circuits are provided by V_{CC} (pin 40). As shown in Figure 5 under normal operating conditions the RESET input is a logic high holding the internal switch in the closed position. V_{CC} is supplied to the program selectable portion of the RAM array through the closed contact of the internal switch. The normally closed contacts of the switch also provide charging power to the external NiCad cells. In the event of power failure, the RESET pin must be pulled low before V_{CC} drops below 4.5 volts in order to guarantee the RAM will not lose data. When the RESET pin becomes a logic low (0V) the internal switch is forced to the open condition. DC power to sustain the desired RAM data is provided by the two NiCad batteries (approximately 2.2 volts). Normally, approximately 5 volts are required to provide RAM data protection in the event of a power failure. National's innovative advances in NMOS technology provide the user with a RAM that requires 50% less voltage and 10% of the power to protect data during power failure. The on-chip charging circuit and lower RAM power requirements provide the user with a twofold saving; no external circuits required for the battery charging and only 2 NiCad cells as opposed to the normal requirement of 4 to 5 NiCad cells.



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FIGURE 5. INS8049 Battery Charging Circuit

Table 1 details the 96 instructions common to both the microcomputers and the microprocessors. The table provides the mnemonic, function and description, instruction code, number of cycles and, where applicable, flag settings.

Table 1 Instruction Set

MNEMONIC	FUNCTION	DESCRIPTION	CYCLES	BYTES	FLAGS		
					C	AC	F0/F1
CONTROL							
EN I		Enable the External Interrupt input.	1	1			
DIS I		Disable the External Interrupt input.	1	1			
ENT0 CLK		Enable T0 as the Clock Output.	1	1			
SEL MB0	(DBF) ← 0	Select Bank 0 (locations 0 - 2047) of Program Memory.	1	1			
SEL MB1	(DBF) ← 1	Select Bank 1 (locations 2048 - 4095) of Program Memory.	1	1			
SEL RB0	(BS) ← 0	Select Bank 0 (locations 0 - 7) of Data Memory.	1	1			
SEL RB1	(BS) ← 1	Select Bank 1 (locations 24 - 31) of Data Memory.	1	1			
DATA MOVES							
MOV A, #data	(A) ← data	Move Immediate the specified data into the Accumulator.	2	2			
MOV A, Rr	(A) ← (Rr); r = 0 - 7	Move the contents of the designated registers into the Accumulator.	1	1			
MOV A, @ Rr	(A) ← ((Rr)); r = 0 - 1	Move Indirect the contents of data memory location into the Accumulator.	1	1			
MOV A, PSW	(A) ← (PSW)	Move contents of the Program Status Word into the Accumulator.	1	1			
MOV Rr, #data	(Rr) ← data; r = 0 - 7	Move Immediate the specified data into the designated register.	2	2			
MOV Rr, A	(Rr) ← (A); r = 0 - 7	Move Accumulator contents into the designated register.	1	1			
MOV @ Rr, A	((Rr)) ← (A); r = 0 - 1	Move Indirect Accumulator contents into data memory location.	1	1			
MOV @ Rr, #data	((Rr)) ← data; r = 0 - 1	Move Immediate the specified data into data memory.	2	2			
MOV PSW, A	(PSW) ← (A)	Move contents of Accumulator into the Program Status Word.	1	1	•	•	•
MOVP A, @ A	(PC 0 - 7) ← (A) (A) ← ((PC))	Move the content of program memory location in the current page addressed by the content of accumulator into the accumulator.	2	1			
MOVP3 A, @ A	(PC 0 - 7) ← (A) (PC 8 - 10) ← 011 (A) ← ((PC))	Move the content of program memory location in page 3 address by the content of accumulator into the accumulator.	2	1			
MOVX A, @ R	(A) ← ((Rr)); r = 0 - 1	Move Indirect the contents of external data memory into the Accumulator.	2	1			

Table 1. Instruction Set (Cont'd.)

MNEMONIC	FUNCTION	DESCRIPTION	CYCLES	BYTES	FLAGS		
					C	AC	F0/F1
DATA MOVES (Cont'd.)							
MOVX @R, A	((Rr) ← (A); r = 0 - 1	Move Indirect the contents of the Accumulator into external data memory.	2	1			
XCH A, Rr	(A) ↔ (Rr); r = 0 - 7	Exchange the Accumulator and designated register's contents.	1	1			
XCH A, @Rr	(A) ↔ ((Rr)); r = 0 - 1	Exchange Indirect contents of Accumulator and location in data memory.	1	1			
XCHD A, @Rr	(A0 - A3) ↔ (((Rr) 0 - 3); r = 0 - 1	Exchange Indirect 4-bit contents of Accumulator and data memory.	1	1			
TIMER COUNTER							
EN TCNTI		Enable Internal Interrupt Flag for Timer/Counter output.	1	1			
DIS TCNTI		Disable Internal Interrupt Flag for Timer/Counter output.	1	1			
MOV A, T	(A) ← (T)	Move contents of Timer/Counter into Accumulator.	1	1			
MOV T, A	(T) ← (A)	Move contents of Accumulator into Timer/Counter.	1	1			
STOP TCNT		Stop Count for Event Counter.	1	1			
STRT CNT		Start Count for Event Counter.	1	1			
STRT T		Start Count for Timer.	1	1			
ACCUMULATOR							
ADD A, #data	(A) ← (A) + data	Add Immediate the specified Data to the Accumulator.	2	2	•	•	
ADD A, Rr	(A) ← (A) + (Rr) for r = 0 - 7	Add contents of designated register to the Accumulator.	1	1	•	•	
ADD A, @Rr	(A) ← (A) + ((Rr)) for r = 0 - 1	Add Indirect the contents the data memory location to the Accumulator.	1	1	•	•	
ADDC A, #data	(A) ← (A) (C) + data	Add Immediate with carry the specified data to the Accumulator.	2	2	•	•	
ADDC A, Rr	(A) ← (A) + (C) + (Rr) for r = 0 - 7	Add with carry the contents of the designated register to the Accumulator.	1	1	•	•	
ADDC A, @Rr	(A) ← (A) + (C) + ((Rr)) for r = 0 - 1	Add Indirect with carry the contents of data memory location to the Accumulator.	1	1	•	•	
ANL A, #data	(A) ← (A) AND data	Logical AND specified Immediate Data with Accumulator.	2	2			
ANL A, Rr	(A) ← (A) AND (Rr) for r = 0 - 7	Logical AND contents of designated register with Accumulator.	1	1			
ANL A, @Rr	(A) ← (A) AND ((Rr)) for r = 0 - 1	Logical AND Indirect the contents of data memory with Accumulator.	1	1			
CPL A	(A) ← NOT (A)	Complement the contents of the Accumulator.	1	1			
CLR A	(A) ← 0	CLEAR the contents of the Accumulator.	1	1			
DA A		DECIMAL ADJUST the contents of the Accumulator.	1	1	•		
DEC A	(A) ← (A) - 1	DECREMENT by 1 the accumulator's contents.	1	1			
INC A	(A) ← (A) + 1	Increment by 1 the accumulator's contents	1	1			
ORL A, #data	(A) ← (A) OR data	Logical OR specified immediate data with Accumulator.	2	2			
ORL A, Rr	(A) ← (A) OR (Rr) for r = 0 - 7	Logical OR contents of designated register with Accumulator.	1	1			
ORL A, @Rr	(A) ← (A) OR ((Rr)) for r = 0 - 1	Logical OR Indirect the contents of data memory location with Accumulator.	1	1			

Table 1. Instruction Set (Cont'd.)

MNEMONIC	FUNCTION	DESCRIPTION	CYCLES	BYTES	FLAGS			
					C	A	F0	F1
ACCUMULATOR (Cont'd.)								
RLA	$(An+1) \leftarrow (An)$ for $n = 0-6$ $(A0) \leftarrow (A7)$	Rotate Accumulator left by 1-bit without carry.	1	1				
RLC A	$(An+1) \leftarrow (An); n = 0-6$ $(A0) \leftarrow (C)$ $(C) \leftarrow (A7)$	Rotate Accumulator left by 1-bit through carry.	1	1	•			
RR A	$(An) \leftarrow (An+1); n = 0-6$ $(A7) \leftarrow (A0)$	Rotate Accumulator right by 1-bit without carry.	1	1				
RRC A	$(An) \leftarrow (An+1); n = 0-6$ $(A7) \leftarrow (C)$ $(C) \leftarrow (A0)$	Rotate Accumulator right by 1-bit through carry.	1	1	•			
SWAP A	$(A4-A7) \leftrightarrow (A0-A3)$	Swap the 2, 4-bit nibbles in the Accumulator.	1	1				
XRL A, #data	$(A) \leftarrow (A) \text{ XOR } \text{data}$	Logical XOR immediate specified data with Accumulator.	2	2				
XRL A, Rr	$(A) \leftarrow (A) \text{ XOR } (Rr)$ for $r = 0-7$	Logical XOR contents of designated register with Accumulator.	1	1				
XRL A, @ Rr	$(A) \leftarrow (A) \text{ XOR } ((Rr))$ for $r = 0-1$	Logical XOR Indirect the contents of data memory location with Accumulator.	1	1				
BRANCH								
DJNZ Rr, addr	$(Rr) \leftarrow (Rr) - 1; r = 0-7$ if $(Rr) \neq 0$; $(PC+0-7) \leftarrow \text{addr}$	Decrement the specified register and test contents.	2	2				
JBb addr	$(PC+0-7) \leftarrow \text{addr}$ if $Bb = 1$ $(PC) \leftarrow (PC) + 2$ if $Bb = 0$	Jump to specified address if Accumulator bit is set.	2	2				
JC addr	$(PC+0-7) \leftarrow \text{addr}$ if $C = 1$ $(PC) \leftarrow (PC) + 2$ if $C = 0$	Jump to specified address if carry flag is set.	2	2				
JF0 addr	$(PC+0-7) \leftarrow \text{addr}$ if $F0 = 1$ $(PC) \leftarrow (PC) + 2$ if $F0 = 0$	Jump to specified address if Flag F0 is set.	2	2				
JF1 addr	$(PC+0-7) \leftarrow \text{addr}$ if $F1 = 1$ $(PC) \leftarrow (PC) + 2$ if $F1 = 0$	Jump to specified address if Flag F1 is set.	2	2				
JMP addr	$(PC+8-10) \leftarrow \text{addr}+8-10$ $(PC+0-7) \leftarrow \text{addr}+0-7$ $(PC+11) \leftarrow \text{DBF}$	Direct Jump to specified address within the 2K address block.	2	2				
JMPP @ A	$(PC+0-7) \leftarrow ((A))$	Jump indirect to specified address pointed to by the accumulator in current page.	2	1				
JNC addr	$(PC+0-7) \leftarrow \text{addr}$ if $C = 0$ $(PC) \leftarrow (PC) + 2$ if $C = 1$	Jump to specified address if carry flag is low.	2	2				
JNI addr	$(PC+0-7) \leftarrow \text{addr}$ if $I = 0$ $(PC) \leftarrow (PC) + 2$ if $I = 1$	Jump to specified address if Interrupt is low.	2	2				
JNT0 addr	$(PC+0-7) \leftarrow \text{addr}$ if $T0 = 0$ $(PC) \leftarrow (PC) + 2$ if $T0 = 1$	Jump to specified address if Test 0 is low.	2	2				
JNT1 addr	$(PC+0-7) \leftarrow \text{addr}$ if $T1 = 0$ $(PC) \leftarrow (PC) + 2$ if $T1 = 1$	Jump to specified address if Test 1 is low.	2	2				
JNZ addr	$(PC+0-7) \leftarrow \text{addr}$ if $A \neq 0$ $(PC) \leftarrow (PC) + 2$ if $A = 0$	Jump to specified address if accumulator is non-zero.	2	2				
JTF addr	$(PC+0-7) \leftarrow \text{addr}$ if $TF = 1$ $(PC) \leftarrow (PC) + 2$ if $TF = 0$	Jump to specified address if Timer Flag is set to 1.	2	2				
JT0 addr	$(PC+0-7) \leftarrow \text{addr}$ if $T0 = 1$ $(PC) \leftarrow (PC) + 2$ if $T0 = 0$	Jump to specified address if Test 0 is a 1.	2	2				
JT1 addr	$(PC+0-7) \leftarrow \text{addr}$ if $T1 = 1$ $(PC) \leftarrow (PC) + 2$ if $T1 = 0$	Jump to specified address if Test 1 is a 1.	2	2				
JZ addr	$(PC+0-7) \leftarrow \text{addr}$ if $A = 0$ $(PC) \leftarrow (PC) + 2$ if $A = 1$	Jump to specified address if Accumulator is 0.	2	2				

MNEMONIC	FUNCTION	DESCRIPTION	CYCLES	BYTES	FLAGS		
					C	AC	F0 F1
INPUT/OUTPUT							
ANL BUS, data	(BUS) ← (BUS) AND data	Logical AND Immediate specified data with contents of BUS.	2	2			
ANL Pp, data	(Pp) ← (Pp) AND data; p 1 - 2	Logical AND immediate specified data with designated port (1 or 2).	2	2			
ANLD Pp, A	(Pp) ← (Pp) AND (A0 - A3); p 4-7	Logical AND contents of Accumulator with designated port (4 - 7).	2	1			
IN A, Pp	(A) ← (Pp); p 1-2	Input data from designated port (1 - 2) into Accumulator.	2	1			
INS A, BUS	(A) ← (BUS)	Input strobed BUS data into Accumulator	2	1			
MOVD A, Pp	(A0-A3) ← (Pp); p 4-7 (A4-A7) ← 0	Move contents of designated port (4 - 7) into Accumulator.	2	1			
MOVD Pp, A	(Pp) ← (A0 - A3); p 4 - 7	Move contents of Accumulator to designated port (4 - 7).	2	1			
ORL BUS, #data	(BUS) ← (BUS) OR data	Logical OR Immediate specified data with contents of BUS.	2	2			
ORLD Pp, A	(Pp) ← (Pp) OR (A0 - A3); p 4-7.	Logical OR contents of Accumulator with designated port (4 - 7).	2	1			
ORL Pp, #data	(Pp) ← (Pp) OR data; p 1 - 2.	Logical OR Immediate specified data with designated port (1 - 2).	2	2			
OUTL BUS, A	(BUS) ← (A)	Output contents of Accumulator onto BUS.	2	1			
OUTL Pp, A	(Pp) ← (A); p 1 - 2	Output contents of Accumulator to designated port (1 - 2).	1	1			
REGISTERS							
DEC Rr	(Rr) ← (Rr) - 1; r 0-7	Decrement by 1 contents of designated register.	1	1			
INC Rr	(Rr) ← (Rr) + 1; r 0-7	Increment by 1 contents of designated register.	1	1			
INC @ Rr	((Rr)) ← ((Rr)) + 1; r 0-1.	Increment Indirect by 1 the contents of data memory location.	1	1			
SUBROUTINE							
CALL addr	((SP)) ← (PC) ((SP)) ← (PSW 4-7) (SP) ← (SP) + 1 (PC8-10) ← addr 8-10 (PC 0-7) ← addr 0-7 (PC 11) ← DBF	Call designated Subroutine.	2	2			
RET	(SP) ← (SP) - 1 (PC) ← ((SP))	Return from Subroutine without restoring Program Status Word.	2	1			
RETR	(SP) ← (SP) - 1 (PC) ← ((SP)) (PSW 4-7) ← ((SP))	Return from Subroutine restoring Program Status Word.	2	1	•	•	
FLAGS							
CPL C	(C) ← NOT (C)	Complement Content of carry bit.	1	1	•		
CPL F0	(F0) ← NOT (F0)	Complement Content of Flag F0.	1	1			•
CPL F1	(F1) ← NOT (F1)	Complement Content of Flag F1.	1	1			•
CLR C	(C) ← 0	Clear content of carry bit to 0.	1	1	•		
CLR F0	(F0) ← 0.	Clear content of Flag 0 to 0.	1	1			•
CLR F1	(F1) ← 0	Clear content of Flag 1 to 0.	1	1			•
MISCELLANEOUS							
NOP		No operation	1	1			

Symbol Definitions

SYMBOL	DESCRIPTION
A	The Accumulator
AC	The Auxiliary Carry Flag
addr	Program Memory Address (12 bits)
b	Bit Designator (b = 0 - 7)
BS	The Bank Switch
BUS	The BUS Port
C	Carry Flag
CLK	Clock Signal
CNT	Event Counter
D	Nibble Designator (4 bits)
data	Number or Expression (8 bits)
DBF	Memory Bank Flip-Flop
F ₀ F ₁	Flags 0, 1
I	Interrupt
P	"In-Page" Operation Designator

SYMBOL	DESCRIPTION
P	Port Designator (p = 1, 2 or 4 - 7)
PSW	Program Status Word
r	Register Designator (r = 0, 1 or 0 - 7)
SP	Stack Pointer
T	Timer
TF	Timer Flag
T ₀ T ₁	Testable Flags 0, 1
X	External RAM
#	Prefix for Immediate Data
@	Prefix for Indirect Address
\$	Program Counter's Current Value
(x)	Contents of External RAM Location
((xx))	Contents of Memory Location Addressed by the Contents of External RAM Location.
←	Replaced By

TYPICAL APPLICATIONS

Figure 6 shows a typical way to use the 48-Series Micro-computers in a stand-alone system.

Crystal used is:

- Series resonant
- AT cut
- 1 to 6 MHz or 4 to 11 MHz

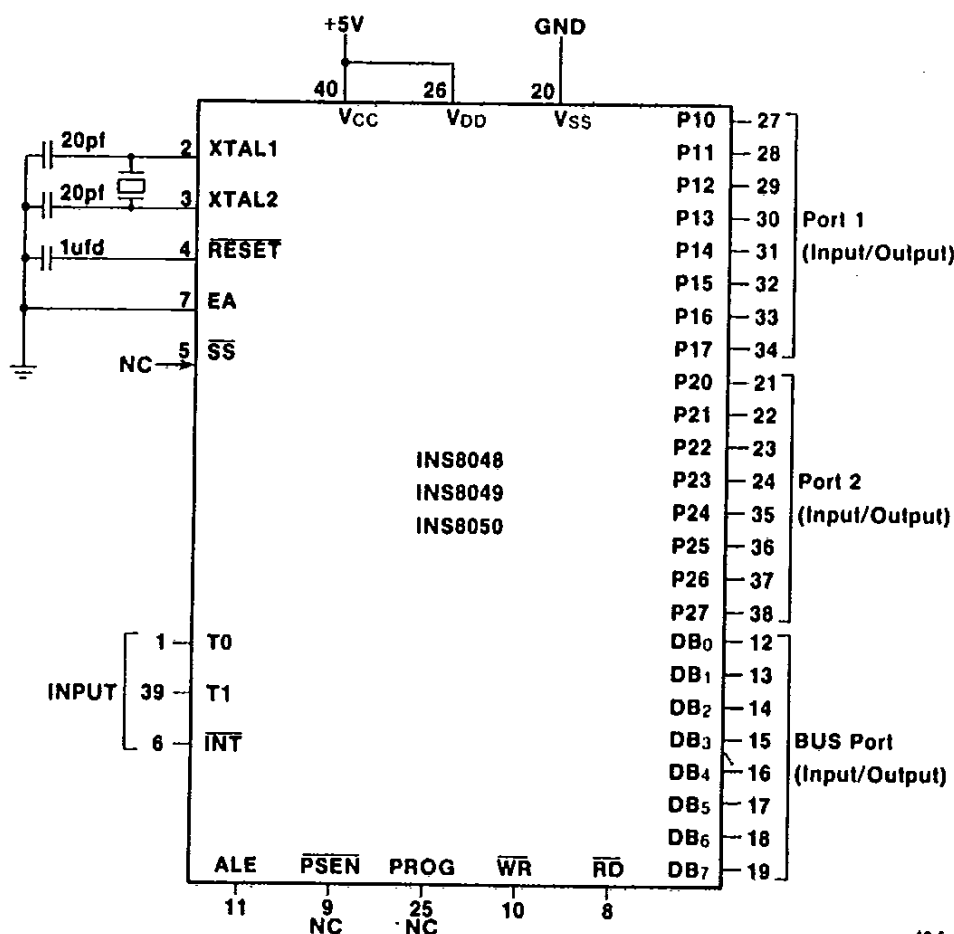
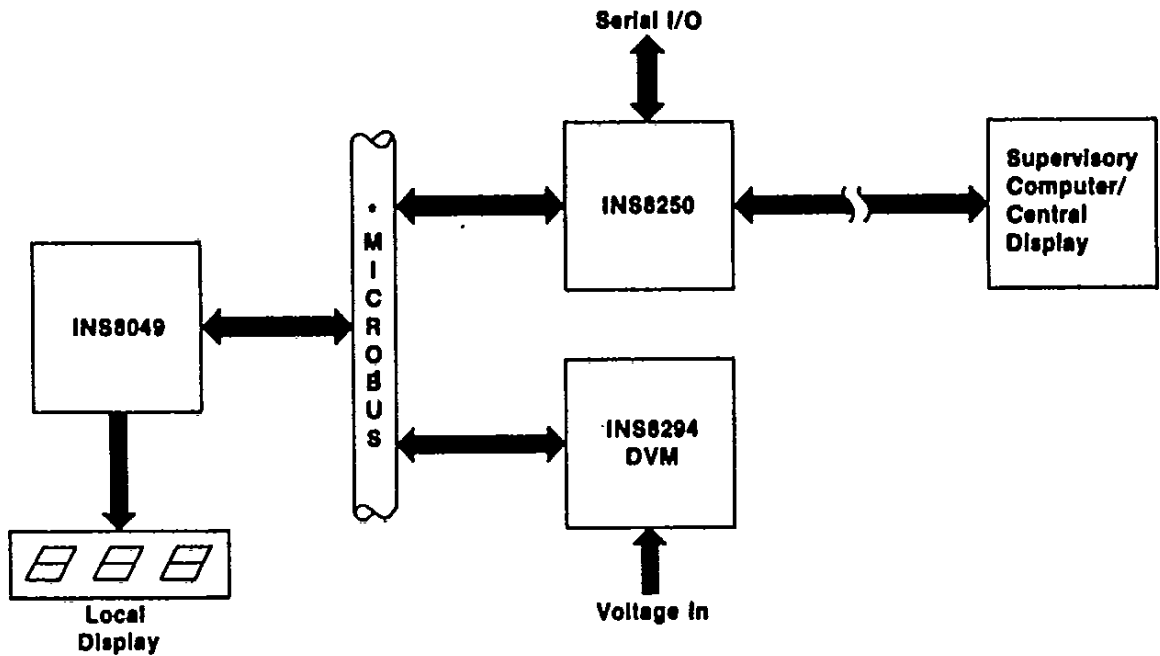


FIGURE 6. Stand-alone INS8048/49/50

TYPICAL APPLICATIONS (Cont'd)

Figure 7 shows a typical remote data acquisition system with an INS8250 Programmable Asynchronous Communication System which can receive commands or update information from a supervisory computer. The figure also shows an INS8294 CMOS DVM that receives data at V_{IN} and displays the data on the 7-segment local display unit. Data are transferred from the INS8294 to the INS8049 via National's MICROBUS™.

**FIGURE 7. Data Acquisition System**

12-7

TYPICAL APPLICATIONS (Cont'd)

Figure 8 shows a typical way to add a Input/Output Expander and Programmable Interval Timer to the 48-Series Microprocessors.

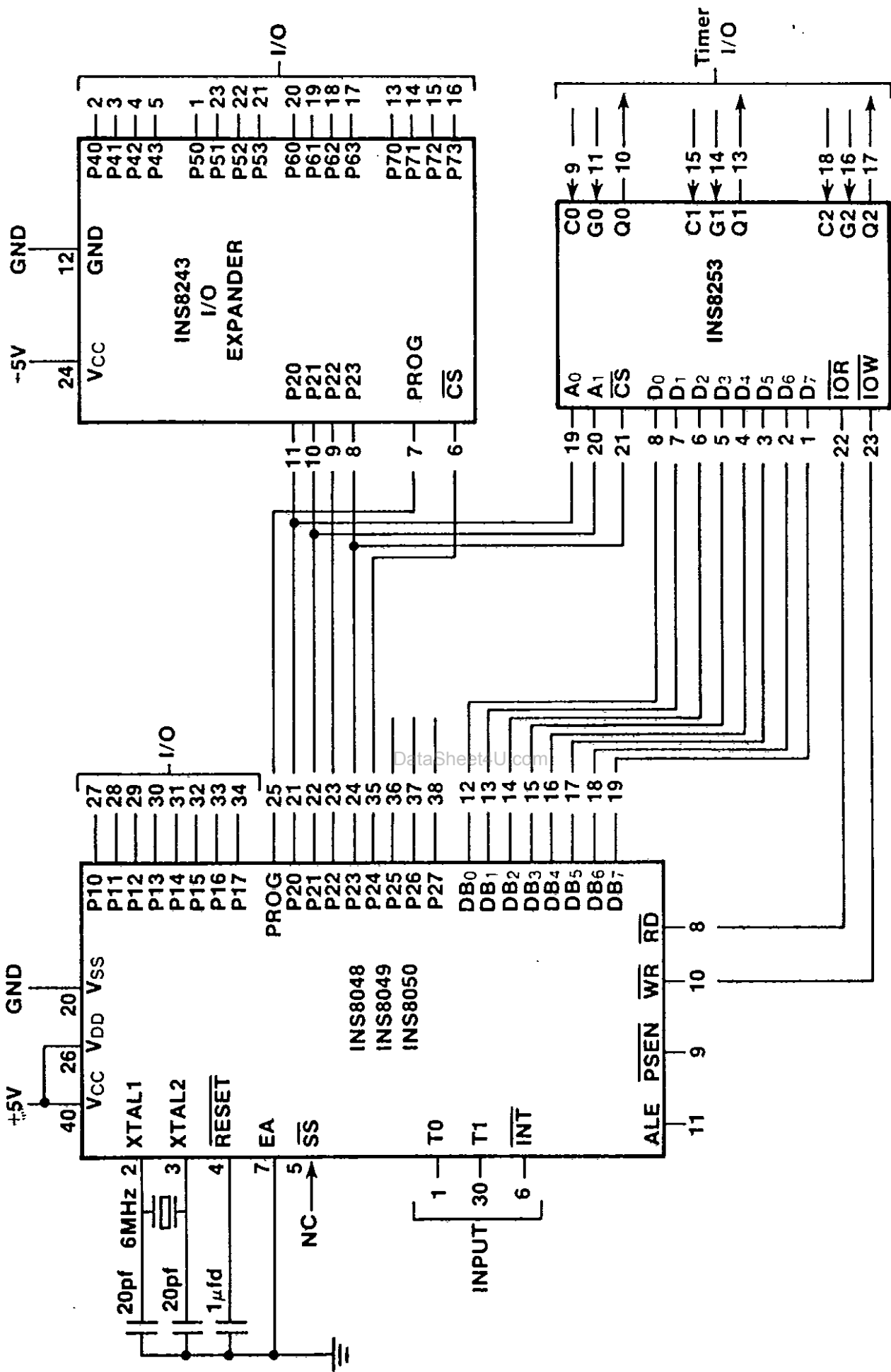


FIGURE 8. INS8253 Interval Timer

APPROVED FORMATS FOR CUSTOM PROGRAMMED PARTS

INPUT MEDIUM:

2716 EPROM
2708 EPROM
PAPER TAPE

IMPORTANT - EPROM LABELLING

Only one customer program may be included in a single order. The following method must be used to identify the EPROMs comprising a program.

a. The EPROMs used for storing a custom program are designated as shown:

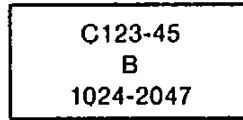
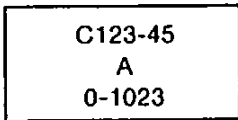
2716:	Block A	0-2047
2708:	Block A	0-1023
	Block B	1024-2047

b. All EPROMs must be labelled (stickers, paint, etc.) with this block designation plus a customer assigned print or identification number.

Example:

- 1) Customer Data
 - Custom Program Length - 2K
 - Medium - Two 2708's
 - Customer Print or I.D. No. C123-45

2) EPROM Labels

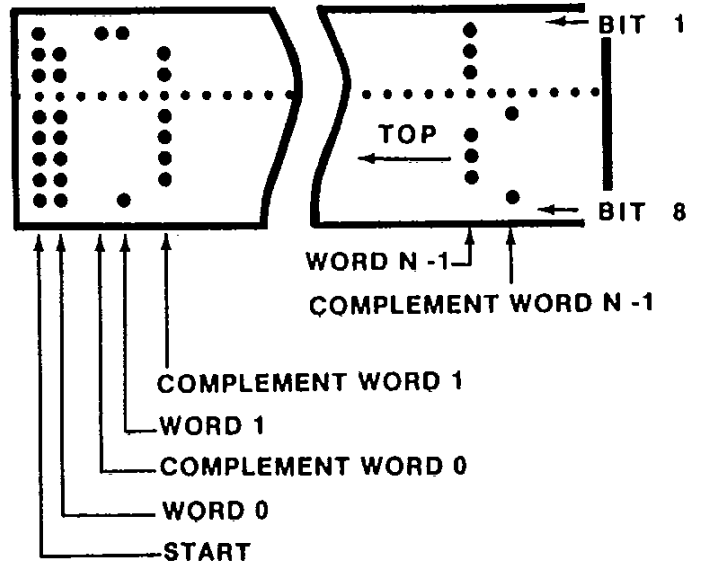


Paper Tape

Tapes may only be submitted in binary complement format. The following information should be written on the paper tape.

Company Name
Customer Print or I.D. No.
NSC Part No.
A Punch = ("1" or "0")
This is _____ logic (POS or NEG)

BINARY COMPLEMENT FORMAT



- NOTE 1:** Tape must be blank except for the data words.
NOTE 2: Tape must start with a rubout character.
NOTE 3: Data is comprised of two words, the first being the actual data and the second being the complement of the data.

Verification

You will receive a listing of the options ordered and the input data. If you also wish to receive EPROMs for verification, please send additional blank EPROMs as necessary for this purpose. You can use software (the listing) or hardware (EPROMs) to verify the program.

You will be asked for a GO/NO GO response within one week after you receive the listing.

VERIFICATION LISTING

The verification listing has six sections:

1. A cover sheet with provision for "STOP, DO NOT PROCEED" or "VERIFICATION CERTIFIED" signatures.
2. Description of the options you have chosen.
3. A description of the log designations and assumptions used to process the data.
4. A listing of the data you have submitted.
5. An error summary.
6. A definition of the standard logic definitions for the ROM and the reduced form of the data. This list shows the output word corresponding to each address coded in binary.

Ordering Information for Custom Programmed Parts

The following information must be submitted with each customer microcomputer program. An order will not be processed unless it is accompanied by this information. This form acts as a Traveler from Customer through Customer Service to ROM programming. Please retain a copy of this form to compare against the verification listing. The form will be sent back to the customer by Customer Service.

	National Microcomputer Part Number
	ROM Letter Code (National Use Only)
Name	Date
Address	Customer Print or I.D. No.
City State Zip	Purchase Order No.
Telephone ()	Name of person National can contact (Print)
Authorized Signature	Date

OPTIONS

1. Device Type (Circle One)

8048-6 (6 MHz) 8049-6 8050-6
 8048-11 (11 MHz) 8049-11

B. Verification Medium: The user will be sent one or more of the following media to verify National's reception of valid date. If any EPROM is selected, blank EPROMs must be submitted with this form.

www.DataSheet4U.com

DataSheet4U.com

DataSheet4U.com

Circle One or More

A. Input Medium (Circle One)

48 Series Part: 8048
 8748

EPROM: 2708 2716
 2758A 2732
 2758B

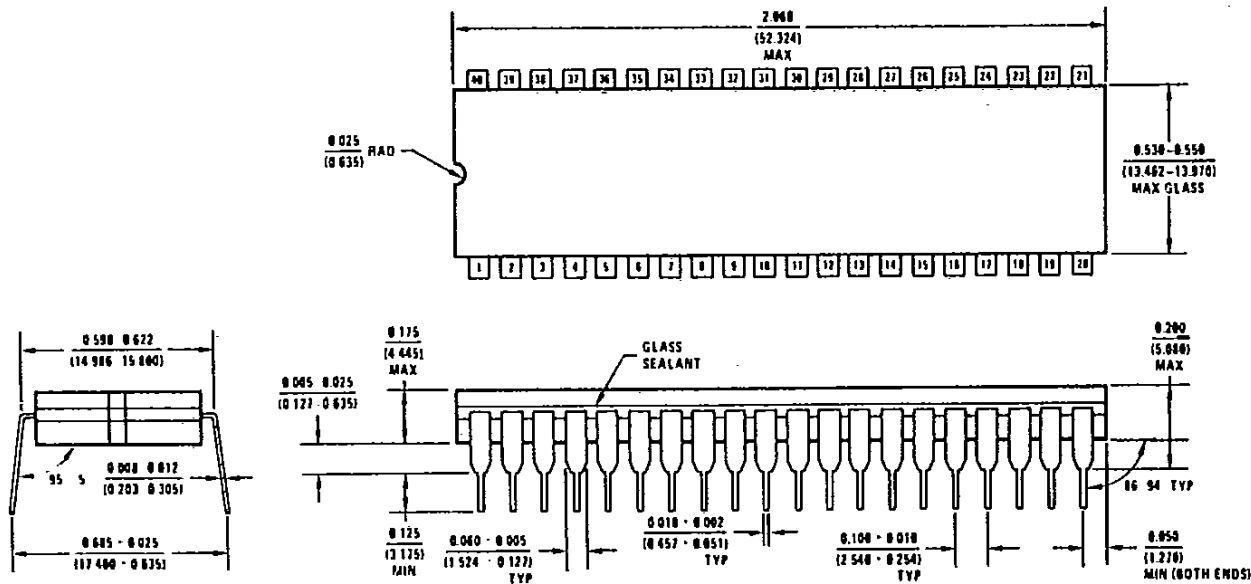
Listing: Binary MPS Format EPROM: 2708 2716
 Hexadecimal Format 2758A 2732
 2758B 8748

Total Number of EPROMs: _____

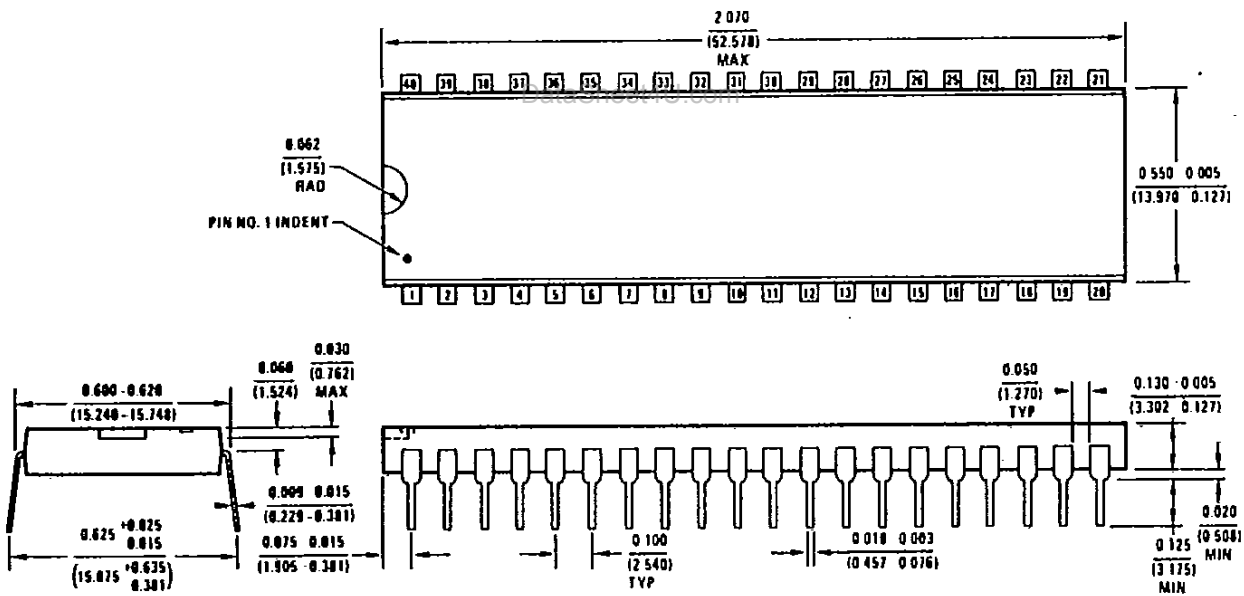
Total number of EPROMs: _____

Physical Dimensions

inches - millimeters



Ceramic Dual-in-Line Package (J)
Order Number INS8048J



Plastic Dual-in-Line Package (N)
Order Number INS8048N



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